

# NX3020NAKV

## 30 V, 200 mA dual N-channel Trench MOSFET

29 October 2013

**Product data sheet** 

### 1. General description

Dual N-channel enhancement mode Field-Effect Transistor (FET) in a ultra small and flat lead SOT666 Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

#### 2. Features and benefits

- Very fast switching
- Trench MOSFET technology
- ESD protection
- Low threshold voltage

### 3. Applications

- · Relay driver
- High-speed line driver
- Low-side loadswitch
- Switching circuits

#### 4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Per transist	or						
$V_{DS}$	drain-source voltage	T <sub>j</sub> = 25 °C		-	-	30	V
V <sub>GS</sub>	gate-source voltage			-20	-	20	V
I <sub>D</sub>	drain current	V <sub>GS</sub> = 4.5 V; T <sub>amb</sub> = 25 °C	[1]	-	-	200	mA
Static chara	cteristics (per transistor)						
R <sub>DSon</sub>	drain-source on-state resistance	$V_{GS}$ = 10 V; $I_{D}$ = 100 mA; $T_{j}$ = 25 °C		-	2.7	4.5	Ω

<sup>[1]</sup> Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 1 cm<sup>2</sup>.



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# 5. Pinning information

**Table 2.** Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	S1	source TR1	6 5 4	D1 D2
2	G1	gate TR1		
3	D2	drain TR2		G1 $G2$ $G2$
4	S2	source TR2	1 2 3	
5	G2	gate TR2	SOT666	
6	D1	drain TR1		S1 S2 017aaa256

# 6. Ordering information

Table 3. Ordering information

Type number	Package				
	Name	Description	Version		
NX3020NAKV	SOT666	plastic surface-mounted package; 6 leads	SOT666		

## 7. Marking

Table 4. Marking codes

Type number	Marking code
NX3020NAKV	GB

# 8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit		
Per transistor								
V <sub>DS</sub>	drain-source voltage	T <sub>j</sub> = 25 °C		-	30	V		
$V_{GS}$	gate-source voltage			-20	20	V		
I <sub>D</sub>	drain current	V <sub>GS</sub> = 4.5 V; T <sub>amb</sub> = 25 °C	[1]	-	200	mA		
		V <sub>GS</sub> = 4.5 V; T <sub>amb</sub> = 100 °C	[1]	-	120	mA		
I <sub>DM</sub>	peak drain current	$T_{amb}$ = 25 °C; single pulse; $t_p \le 10$ μs		-	800	mA		
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> = 25 °C	[2]	-	260	mW		
			[1]	-	370	mW		
		T <sub>sp</sub> = 25 °C		-	1100	mW		

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Symbol	Parameter	Conditions		Min	Max	Unit			
Source-drain	Source-drain diode								
I <sub>S</sub>	source current	T <sub>amb</sub> = 25 °C		-	200	mA			
Per device	Per device								
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> = 25 °C	[2]	-	375	mW			
T <sub>j</sub>	junction temperature			-55	150	°C			
T <sub>amb</sub>	ambient temperature			-55	150	°C			
T <sub>stg</sub>	storage temperature			-65	150	°C			

- [1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 1 cm<sup>2</sup>.
- [2] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

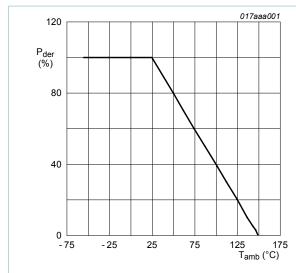


Fig. 1. Normalized total power dissipation as a function of ambient temperature

$$P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}C)}} \times 100 \%$$

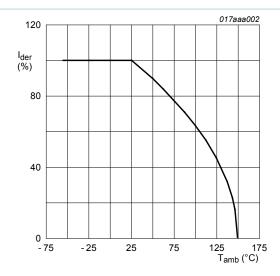


Fig. 2. Normalized continuous drain current as a function of ambient temperature

$$I_{der} = \frac{I_D}{I_{D(25^{\circ}\text{C})}} \times 100 \%$$

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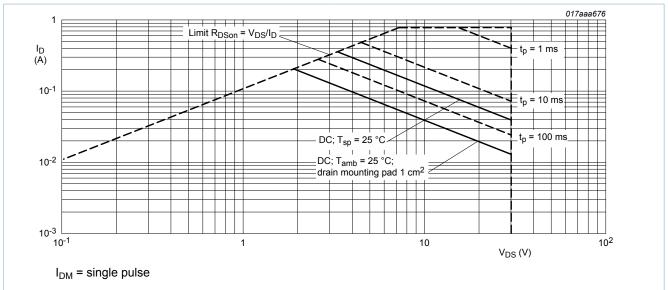


Fig. 3. Safe operating area; junction to ambient; continuous and peak drain currents as a function of drain-source voltage

#### 9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Per transistor			1				_
R <sub>th(j-a)</sub> thermal resistance from junction to ambient		in free air	[1]	-	410	480	K/W
	_		[2]	-	290	340	K/W
$R_{th(j-sp)}$	thermal resistance from junction to solder point			-	-	105	K/W

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 1 cm<sup>2</sup>.

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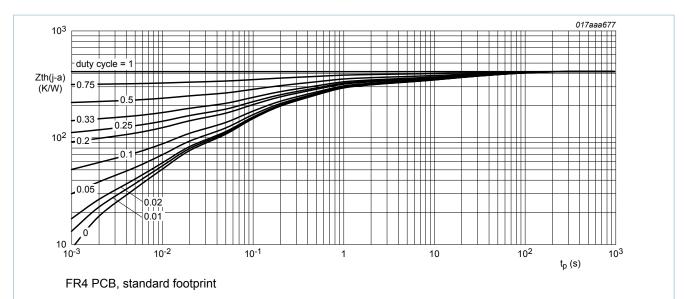


Fig. 4. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

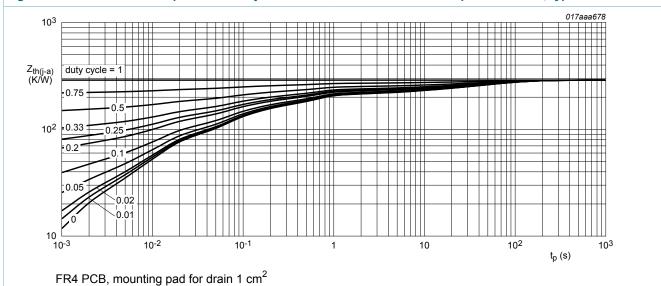


Fig. 5. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

#### 10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	acteristics (per transistor)		'			
$V_{(BR)DSS}$	drain-source breakdown voltage	$I_D$ = 250 $\mu$ A; $V_{GS}$ = 0 V; $T_j$ = 25 °C	30	-	-	V
$V_{GSth}$	gate-source threshold voltage	$I_D = 250 \ \mu\text{A}; \ V_{DS} = V_{GS}; \ T_j = 25 \ ^{\circ}\text{C}$	8.0	1.2	1.5	V
I <sub>DSS</sub>	drain leakage current	$V_{DS} = 30 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	-	1	μA
		V <sub>DS</sub> = 30 V; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 150 °C	-	-	10	μA
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Symbol	Parameter	Conditions	Min	Тур	Max	Unit
I <sub>GSS</sub>	gate leakage current	V <sub>GS</sub> = 20 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	-	3.5	μΑ
		V <sub>GS</sub> = -20 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	-	3.5	μΑ
		V <sub>GS</sub> = 10 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	-	1	μA
		V <sub>GS</sub> = -10 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	-	1	μA
		V <sub>GS</sub> = 4.5 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	-	0.5	μA
		$V_{GS} = -4.5 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 ^{\circ}\text{C}$	-	-	0.5	μA
R <sub>DSon</sub>	drain-source on-state	$V_{GS}$ = 10 V; $I_D$ = 100 mA; $T_j$ = 25 °C	-	2.7	4.5	Ω
	resistance	V <sub>GS</sub> = 10 V; I <sub>D</sub> = 100 mA; T <sub>j</sub> = 150 °C	-	5.5	9.2	Ω
		V <sub>GS</sub> = 4.5 V; I <sub>D</sub> = 100 mA; T <sub>j</sub> = 25 °C	-	3	5.2	Ω
		$V_{GS} = 2.5 \text{ V}; I_D = 10 \text{ mA}; T_j = 25 ^{\circ}\text{C}$	-	4	13	Ω
9 <sub>fs</sub>	forward transconductance	V <sub>DS</sub> = 10 V; I <sub>D</sub> = 150 mA; T <sub>j</sub> = 25 °C	-	320	-	mS
Dynamic c	haracteristics (per transist	or)	· ·	'	'	
Q <sub>G(tot)</sub>	total gate charge	V <sub>DS</sub> = 15 V; I <sub>D</sub> = 150 mA; V <sub>GS</sub> = 4.5 V;	-	0.34	0.44	nC
Q <sub>GS</sub>	gate-source charge	T <sub>j</sub> = 25 °C	-	0.11	-	nC
$Q_{GD}$	gate-drain charge		-	0.06	-	nC
C <sub>iss</sub>	input capacitance	V <sub>DS</sub> = 10 V; f = 1 MHz; V <sub>GS</sub> = 0 V;	-	13	20	pF
C <sub>oss</sub>	output capacitance	T <sub>j</sub> = 25 °C	-	2.6	-	pF
C <sub>rss</sub>	reverse transfer capacitance		-	1.1	-	pF
t <sub>d(on)</sub>	turn-on delay time	$V_{DS}$ = 20 V; $R_L$ = 250 $\Omega$ ; $V_{GS}$ = 10 V;	-	5	10	ns
t <sub>r</sub>	rise time	$R_{G(ext)} = 6 \Omega$ ; $T_j = 25 °C$	-	5	-	ns
t <sub>d(off)</sub>	turn-off delay time		-	34	68	ns
t <sub>f</sub>	fall time		-	17	-	ns
Source-dra	in diode (per transistor)				1	
$V_{SD}$	source-drain voltage	$I_S$ = 115 mA; $V_{GS}$ = 0 V; $T_j$ = 25 °C	0.47	0.7	1.2	V

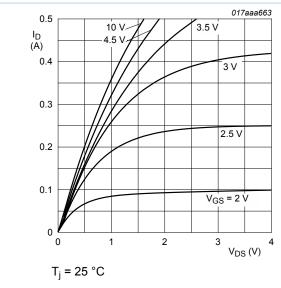


Fig. 6. Output characteristics: drain current as a function of drain-source voltage; typical values

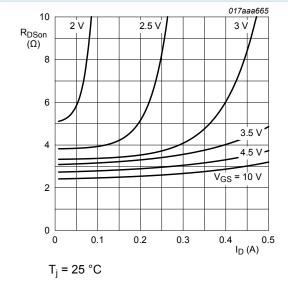


Fig. 8. Drain-source on-state resistance as a function of drain current; typical values

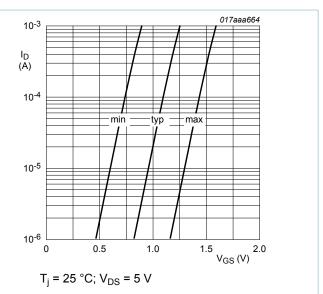


Fig. 7. Sub-threshold drain current as a function of gate-source voltage

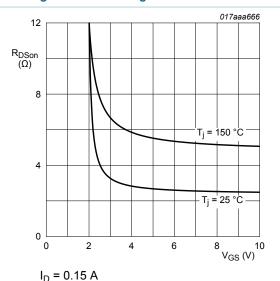


Fig. 9. Drain-source on-state resistance as a function of gate-source voltage; typical values

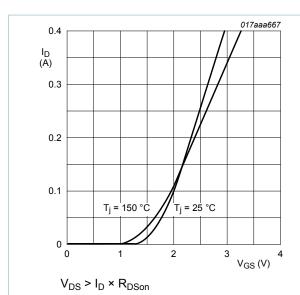


Fig. 10. Transfer characteristics: drain current as a function of gate-source voltage; typical values

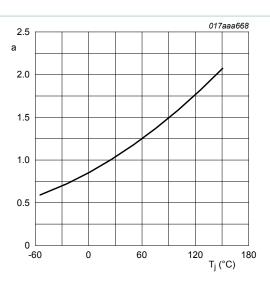


Fig. 11. Normalized drain-source on-state resistance as a function of junction temperature; typical values

$$a = \frac{R_{DSon}}{R_{DSon(25^{\circ}C)}}$$

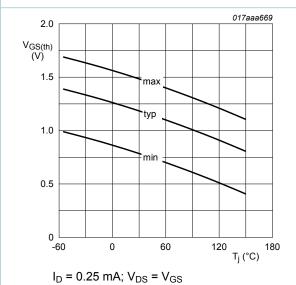
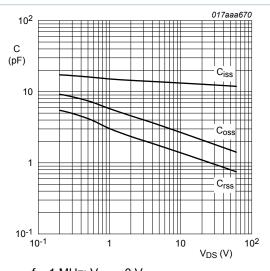


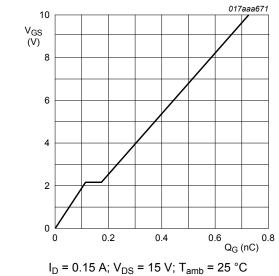
Fig. 12. Gate-source threshold voltage as a function of junction temperature



 $f = 1 MHz; V_{GS} = 0 V$ 

Fig. 13. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

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charge; typical values

I<sub>D</sub> = 0.15 A; V<sub>DS</sub> = 15 V; T<sub>amb</sub> = 25 °C Fig. 14. Gate-source voltage as a function of gate

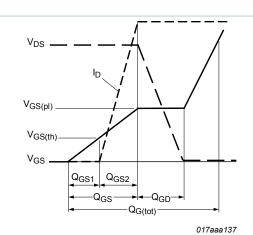


Fig. 15. Gate charge waveform definitions

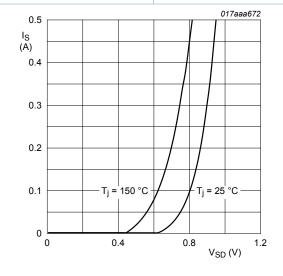
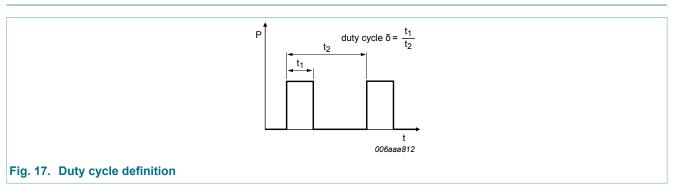


Fig. 16. Source current as a function of source-drain voltage; typical values

### 11. Test information

 $V_{GS} = 0 V$ 



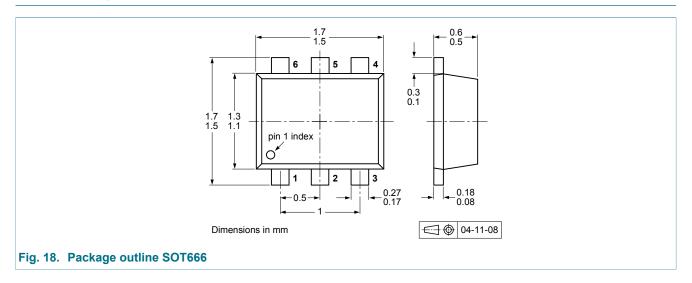
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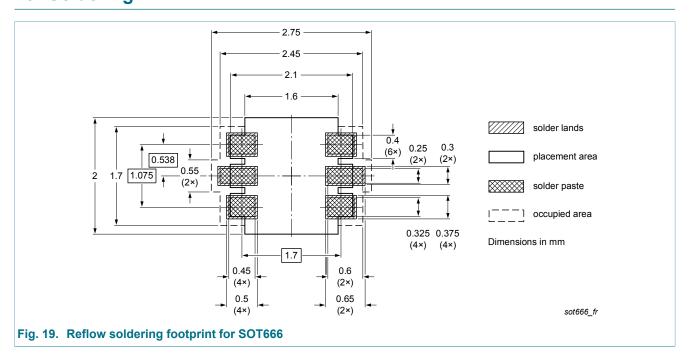
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## 12. Package outline



## 13. Soldering



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# 14. Revision history

#### Table 8. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes		
NX3020NAKV v.2	20131029	Product data sheet	-	NX3020NAKV v.1		
Modifications:	<ul> <li>3D package outline added</li> <li>Table 7 values of capacitance parameters corrected</li> <li>Figure 13 corrected</li> </ul>					
NX3020NAKV v.1	20120706	Product data sheet	-	-		

#### 30 V, 200 mA dual N-channel Trench MOSFET

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Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- Please consult the most recently issued document before initiating or completing a design.
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